

5 é / Descriptions

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Ultrafast Recovery Diode in a TO-220AC Plastic Package.

α^a / Features

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Silicon epitaxial process to produce ultrafast recovery diode with low reverse leakage current and high reliability.

Đ ÷ / Applications

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For high frequency, high voltage, high current rectifier diode, freewheeling diode.

Ã W] Ô • / Equivalent Circuit

• Û - æ / Pinning

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PIN1 o • 2 y Cathode

PIN 3 y Anode

Z Ü B , M V / h_{FE} Classifications & Marking

• - ~ ^a øž See Marking Instructions

Table 1 / Absolute Maximum Ratings(Ta=25 °C ;)

Parameter	Symbol	Rating	Unit
Peak Repetitive Reverse Voltage	V_{RRM}	600	V
RMS Voltage	V_{RMS}	420	V
DC Blocking Voltage	V_{DC}	600	V
Average Forward Current	I_F	1 h 10	A
Peak forward surge current	I_{FSM}	100	A
Typical Thermal Resistance Junction to Case	R_{Jc}	1.5	/W
Junction Temperature Range	T_j	150	
Storage Temperature Range	T_{stg}	-55 ~ 150	

Table 2 / Electrical Characteristics(Ta=25 °C ;)

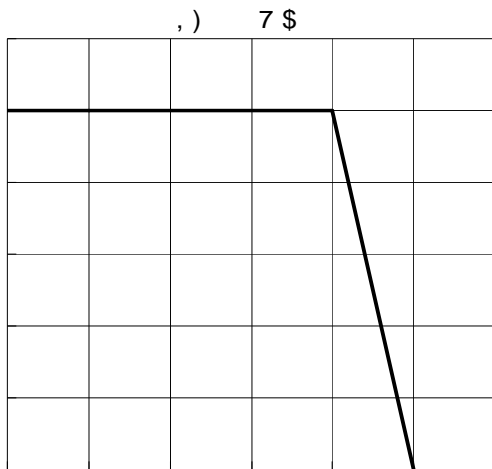
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse Voltage	V_R	$I_R=1mA$	600			V
Forward Voltage	V_F	$I_F=2.0A$ $T_C=25$		1.0	1.2	V
		$I_F=2.0A$ $T_C=150$		0.73	1.0	
		$I_F=10A$ $T_C=25$		1.3	1.5	
		$I_F=10A$ $T_C=150$		1.1	1.2	
Instantaneous Reverse Current(Note1)	I_R	$V_R=600V$ $T_a=25$			10	A
		$V_R=480V$ $T_a=150$			100	
		$V_R=600V$ $T_a=150$			500	
Reverse Recovery Time	t_{rr}	$I_F=0.5A$ $I_{RR}=0.25A$			50	ns

Notes

1. Short duration pulse test used to minimize self-heating effect.

2. Unless otherwise noted, values for the parameters of a single chip

Ô ? d • Ž ¢ / Electrical Characteristic Curve



BRMUR1060AC

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Company Code

Product Type.

Lot No. Code, code change with Lot No.

